PROCESS CP176

Power Transistor

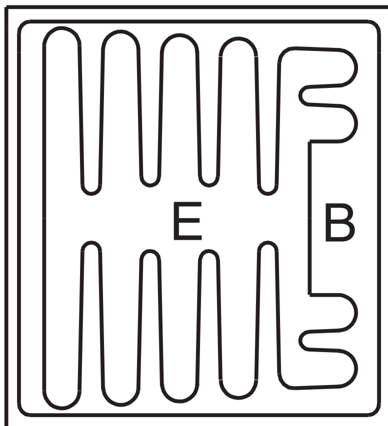
NPN - Amp/Switch Transistor Chip

Central™
Semiconductor Corp.

PROCESS DETAILS

Process	MULTI EPITAXIAL PLANAR
Die Size	203 x 227 MILS
Die Thickness	12.5 ± 1.0 MILS
Base Bonding Pad Area	38 x 76 MILS
Emitter Bonding Pad Area	47 x 72 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Ag - 10,000Å

GEOMETRY



BACKSIDE COLLECTOR R0

GROSS DIE PER 4 INCH WAFER

240

PRINCIPAL DEVICE TYPES

MJ15003

145 Adams Avenue
Hauppauge, NY 11788 USA
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Fax: (631) 435-1824
www.centralsemi.com

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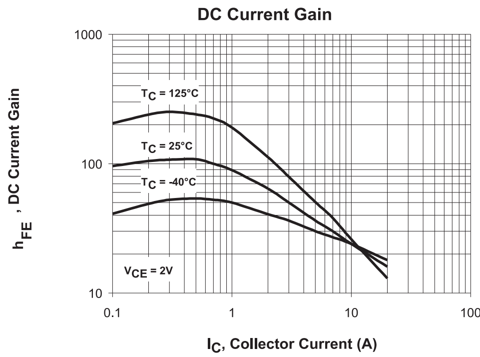
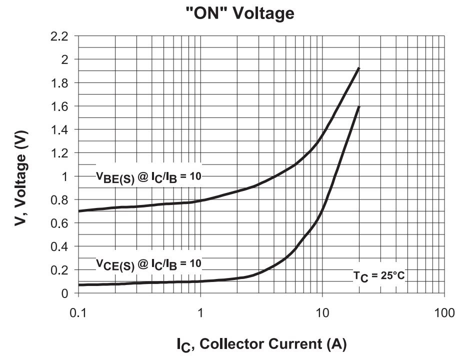
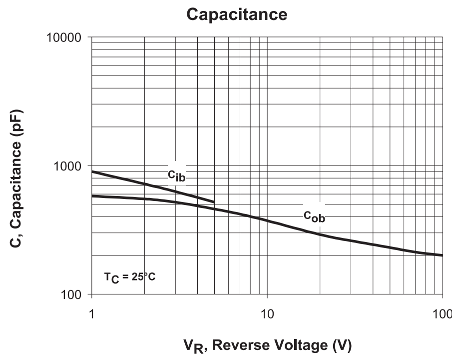
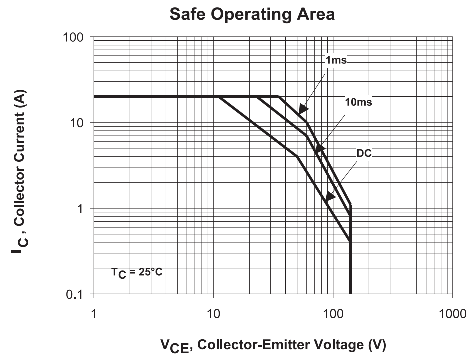
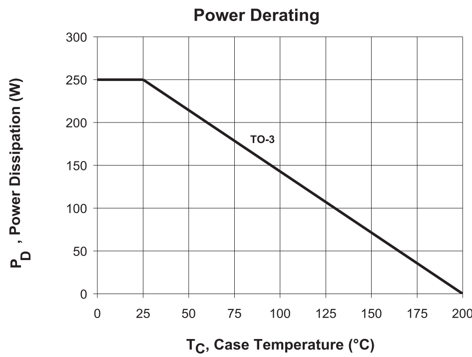
Typical Electrical Characteristics

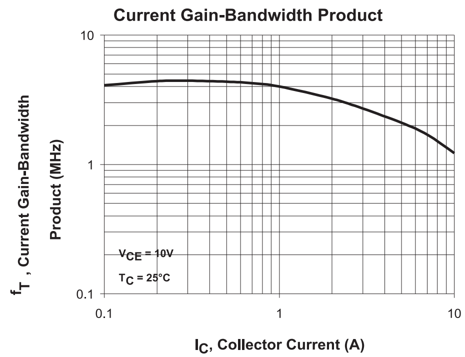












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